DISCRETE SEMICONDUCTORS

DATA SHEET

BFQ262; BFQ262A NPN video transistors

Product specification Supersedes data of November 1995 File under Discrete Semiconductors, SC05

1997 Oct 02





NPN video transistors

BFQ262; **BFQ262A**

FEATURES

- · High breakdown voltages
- Low output capacitance
- Optimum temperature profile
- · Good thermal stability
- Excellent reliability properties.

APPLICATIONS

• Buffer/driver in high-resolution colour graphics monitors.

DESCRIPTION

NPN video transistor in a SOT32 (TO-126) plastic package.

PINNING

PIN	DESCRIPTION					
1	emitter					
2	collector					
3	base					

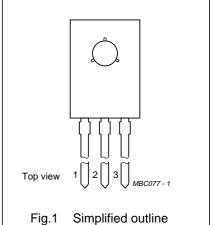


Fig.1 Simplified outline (SOT32; TO-126).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter				
	BFQ262		_	_	100	V
	BFQ262A		_	_	115	V
V _{CER}	collector-emitter voltage	R _{BE} = 100 Ω				
	BFQ262		_	_	95	V
	BFQ262A		_	_	110	V
I _C	collector current (DC)		_	_	400	mA
P _{tot}	total power dissipation	T _s ≤ 85 °C; note 1	_	_	5	W
h _{FE}	DC current gain	$I_C = 100 \text{ mA}; V_{CE} = 10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$				
	BFQ262		50	60	_	
	BFQ262A		20	35	_	
f _T	transition frequency	I _C = 100 mA; V _{CE} = 10 V; f = 100 MHz;				
	BFQ262	T _{amb} = 25 °C	1	1.4	_	GHz
	BFQ262A		0.8	1.2	_	GHz

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BFQ262		_	100	V
	BFQ262A		_	115	V
V _{CEO}	collector-emitter voltage	open base			
	BFQ262		_	65	V
	BFQ262A		_	95	V
V_{CER}	collector-emitter voltage	R _{BE} = 100 Ω			
	BFQ262		_	95	V
	BFQ262A		_	110	V
V _{EBO}	emitter-base voltage	open collector	_	3	V
I _C	collector current (DC)		_	400	mA
P _{tot}	total power dissipation	T _s ≤ 85 °C; note 1; see Fig.3	_	5	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	175	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	$T_s \le 85$ °C; note 1	18	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

^{1.} $T_{\mbox{\scriptsize S}}$ is the temperature at the soldering point of the collector pin.

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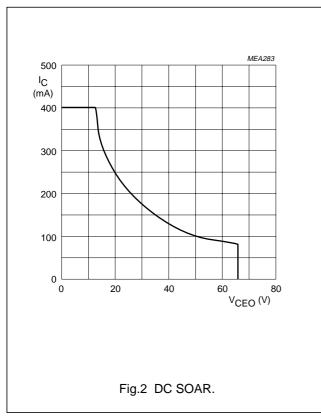
CHARACTERISTICS

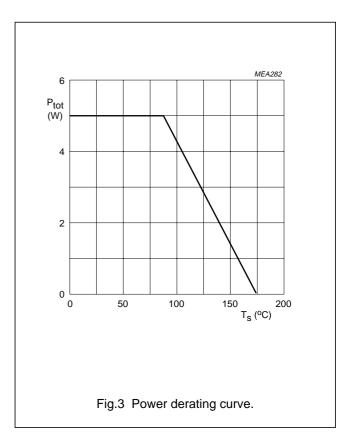
 T_j = 25 °C unless otherwise specified.

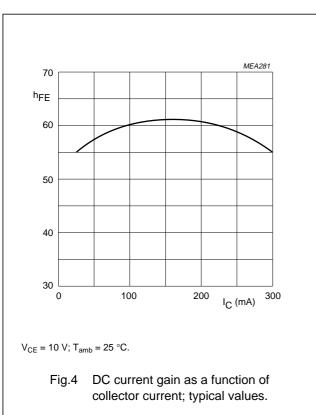
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 0.1 \text{ mA}; I_E = 0$				
	BFQ262		100	_	-	V
	BFQ262A		115	_	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 10 mA; I _B = 0				
	BFQ262		65	_	-	V
	BFQ262A		95	_	-	V
V _{(BR)CER}	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; R_{BE} = 100 \Omega$				
	BFQ262		95	_	_	V
	BFQ262A		110	_	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = 0.1 mA; I _C = 0	3	_	_	V
I _{CES}	collector-emitter cut-off current	I _B = 0; V _{CE} = 50 V	_	_	100	μΑ
I _{CBO}	collector-base cut-off current	I _E = 0; V _{CB} = 50 V	_	_	20	μΑ
h _{FE}	DC current gain	I _C = 100 mA; V _{CE} = 10 V;				
	BFQ262	T _{amb} = 25 °C; see Fig.4	50	60	_	
	BFQ262A		20	35	-	
f _T	transition frequency	I _C = 100 mA; V _{CE} = 10 V;				
	BFQ262	f = 100 MHz; T _{amb} = 25 °C;	1	1.4	_	GHz
	BFQ262A	see Fig.6	0.8	1.2	_	GHz
C _{cb}	collector-base capacitance	$I_C = I_c = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$; $T_{amb} = 25 ^{\circ}\text{C}$; see Fig.5	-	2	_	pF
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	3.5	_	pF

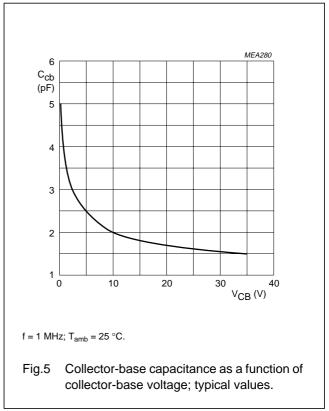
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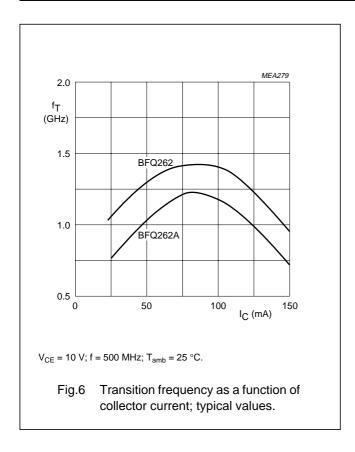






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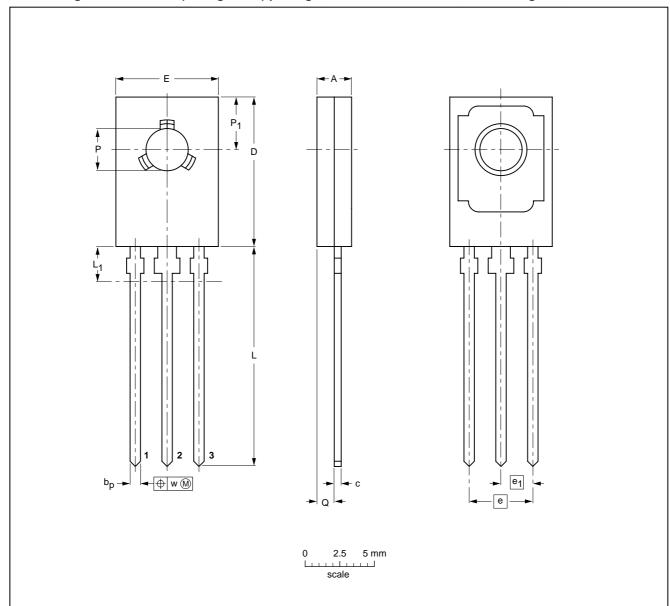


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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32



DIMENSIONS (mm are the original dimensions)

UNIT	Α	bp	С	D	E	е	e ₁	L	L ₁ ⁽¹⁾ max	Q	Р	P ₁	w
mm	2.7 2.3	0.88 0.65	0.60 0.45	11.1 10.5	7.8 7.2	4.58	2.29	16.5 15.3	2.54	1.5 0.9	3.2 3.0	3.9 3.6	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT32		TO-126				97-03-04

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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NOTES

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